

S.E. (Comp.) (Semester – I) Examination, 2010 ELECTRONIC DEVICES & CIRCUITS (2003 Course)

Time: 3 Hours

Max. Marks: 100

Instructions: 1) Answer any three questions from each Section.

- Answers to the two Sections should be written in separate books.
- 3) Neat diagrams must be drawn wherever necessary.
- 4) Black figures to the right indicate full marks.
- 5) Use of electronic pocket calculator is allowed.
- 6) Assume suitable data, if necessary.

SECTION - I

- 1. A) The circuit in fig. 1 uses a silicon transistor with current gain (β) 200 & $V_{CEQ} = 3V$. For the output voltage (V_o) to be zero
 - i) Determine the value of collector resistance and emitter resistance.

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ii) With reference to the values in part (1) above, find the new value of V_0 if β is 100.

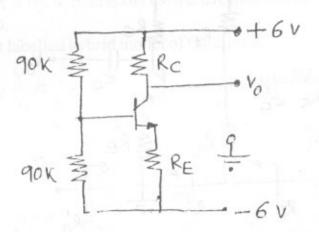


Fig. 1

B) Explain Thermal Runaway.



- 2. A) Calculate stability factor for a transistor circuit to be thermally stable if the specifications are as under
 - Transistor used is NPN and is operated in self bias arrangement
 - The component values are $R_C = 1k$ and $R_E = 0.1 K$
 - The parameter values are $I_{CO} = 1.2 \text{ nA}$, $\theta = 10 \times 10^8 \text{ °C/W}$, $V_{CEO} = 5.5 \text{ V}$
 - The power supply used is +10 volts.

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- B) Explain with necessary illustrations, what happens when
 - i) Operating point is located closer to saturation region

- ii) Operating point is located closer to cutoff region.
- 3. A) For the circuit in fig. 2
 - i) Draw the small signal hybrid model.

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- ii) Derive in terms of h parameter and circuit component the equations for a) current gain A₁ and A_{1S} b) Voltage gain A₂ and A_{VS} c) Input impedance
 - R_i' and R_i d) output impedance R_O and R'_o.

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B) Justify "CE is the only transistor configuration to produce phase shift between input and output signal".

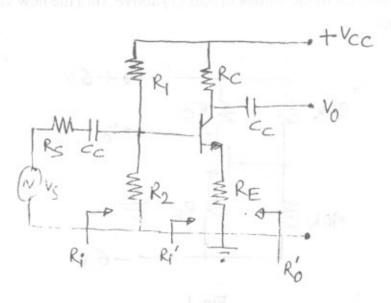


Fig. 2



- 4. A) For the circuit in fig. (3), the transistor h parameters are hie = 1k, hfe = 50 and negligible hre and hoe, determine the following
 - $i) A_v = \frac{V_0}{V_s}$
- ii) $A_1 = \frac{i_0}{i_0}$
- iii) R_i
- iv) R'₀

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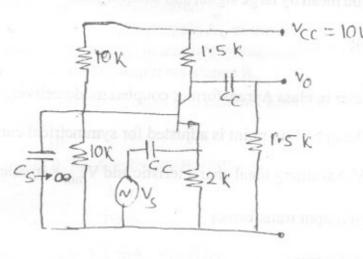


Fig. 3

B) Draw the circuit diagram and explain importance of

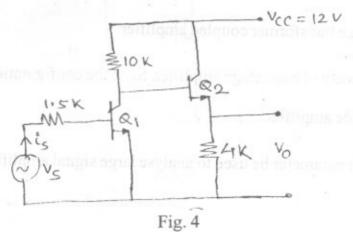
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- i) Bootstrap emitter follower circuit
- ii) Bootstrap darlington pair
- 5. A) For the circuit in fig. 4, transistors used are identical with hie = 2k, hfe = 100, hre = hoe = 0,
 - i) Draw neat labelled hybrid model of the circuit.

2

ii) Determine $\frac{V_o}{V_s} \& \frac{i_o}{i_s}$.

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	B)	Explain harmonic and cross over distortion of a power amplifier with necessary	
		illustrations.	6
	C)	Explain what you mean by large signal and small signal.	2
		OR	
6.	A)	A power transistor in class A transformer coupled mode delivers 5W Power	
	/	to 5Ω load. The operating point is adjusted for symmetrical current swing	
		with $V_{cc} = 18$ V. Assuming ideal characteristic and $V_{min} = 0$, calculate	
		i) turns ratio of output transformer	
		ii) peak collector current	
		iii) Q point coordinates	
		iv) collector circuit efficiency and not an analysis of the collector circuit efficiency	8
	B)	Draw the circuit diagram of two stage	
		i) Direct coupled amplifier	
		ii) R-C coupled amplifier	
		iii) Single stage transformer coupled amplifier.	6
	C)	Explain necessity of multistage amplifier. State the configuration of stages	
		used in cascade amplifier.	2
	D)	Explain can h parameter be used to analyse large signal amplifier.	2



SECTION - II

7		공연 집에 가장하다 사람들의 전투에 가장 사람들이 살아지지 않는데 없었다.	rce follower n channel JFET, consisting	2
	10 10	0 -	nd coupling capacitors C _C .	2
		~	ne circuit in part (1) above.	2
		ation for drain current	u	2
	iv) Obtain equ	ation for voltage gain.	A _V of the circuit.	2
	v) Can this cir	rcuit be used to amplif	y voltage signal. Justify your answer.	2
	vi) Derive equ	ation for output resista	ance R _o	2
	B) Draw the struc	cture and symbol of n	channel EMOSFET. Sketch its transfer	
	characteristics			4
	C)R		
8.	A) For the circuit	in fig. 5, calculate the	following	
	i) g _m	ii) r _d		
	iii) A _v	iv) R _i	v) R _o	10
	Assume I _{D(O)}	$V_{N} = 5.5 \text{ mA}, V_{GS}(C)$	$(N) = 7.5V$, $V_T = 3V$, $Y_{OS} = 50 \mu s$, (3 mA.) Use Miller theorem. Calculate	
	k = 0.25 mA/v	V_{GS}^2 , $V_{GS} = 6.5 \text{ V & I}_D =$	3 mA. Use Miller theorem. Calculate	
		$r(i/p)$ and $R_{eff}(o/p)$.	O. F. witter CEANT recorders	2

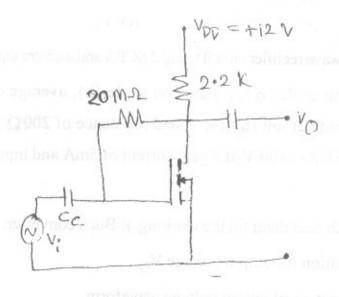


Fig. 5



9.	A)	i)	Draw block diagram of OPAMP.	2
		ii)	Sketch the circuit of level shifter an derive equation for output voltage V_o .	4
		iii)	State disadvantage of level shifter and explain how it can be overcome	
			with the help of necessary circuit.	4
	B)	Di	raw and explain operation of I to V converter circuit using OPAMP. Derive	
		eq	uation for output voltage V _o . State its application.	6
			OR	
10.	A)	i)	Draw using OPAMP a circuit to generate a square wave without any input	
			signal applied to it.	2
		ii)	Explain its operation with the help of waveforms $V_C \& V_O$.	4
		iii)	Derive equation for time period T of the square wave.	4
	B)	Ex	cplain OPAMP parameters	
		i)	CMRR ii) PSRR	
		iii)	Slew rate iv) V _{io} .	6
11.	A)	i)	Draw a full wave rectifier circuit using 2 SCRS and a centre tap transformer.	2
		ii)	Obtain firing angle (α), conduction angle (β), average output voltage	
			(V_o) and load current (i_L) for a load resistance of 200Ω if the forward	
			voltage of SCR is 400 V at a gate current of 5mA and input applied is	
			600 sin wt.	6
	B)	i)	Explain with neat diagram the working of Buck converter.	3
		ii)	Obtain equation for output voltage V _O	3
		iii)	Sketch the nature of output voltage waveform	2
	C)	Sk	etch V-I characteristic of diac	2



12.	(A)	i) State difference between on line and off line UPS.	2
		ii) Explain operation of on line UPS with neat diagram.	4
	B)	i) Explain operation of SCR using two transistor analogy.	3
		ii) Derive equation for anode current I _A .	3
	C)	Define i) Latching current ii) Holding current iii) V _{BO} iv) V _{BR} .	6

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